

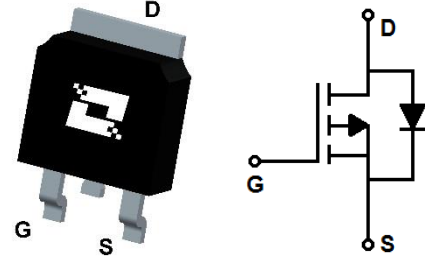
Features

- P-Channel, *Low RDS(on) @VGS=-10V*
- *-5V Logic Level Control*
- *100% UIS Tested*
- *Pb-Free, RoHS Compliant*

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
-100V	60mΩ @-10V	-22A
	69mΩ @-4.5V	

Applications

- Telecom, industrial power supplies
- LED backlighting.
- In PWM Applications
- *Load Switch*


Order Information
TO-252

Product	Package	Marking	Packing
DWD060P10	TO-252	060P10	2500PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit	
Common Ratings (T _j =25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage	±20	V	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	-100	V	
T _J	Maximum Junction Temperature	175	°C	
T _{STG}	Storage Temperature Range	-50 to 150	°C	
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested①	T _C =25°C	-60	A
I _S	Diode continuous forward current	T _C =25°C	-22	A
I _D	Continuous Drain Current	T _C =25°C	-22	A
		T _C =70°C	-17.6	
P _D	Maximum Power Dissipation	T _C =25°C	100	W
EAS	Avalanche energy, single pulsed ②		84	mJ
R _{θJC}	Thermal Resistance-Junction to Case		1.5	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-100	–	–	V
I _{DSS}	Zero Gate Voltage Drain Current(T _C =25°C)	V _{DS} =-100V, V _{GS} =0V	–	–	-1	μA
	Zero Gate Voltage Drain Current(T _C =125°C)	V _{DS} =-80V, V _{GS} =0V	–	–	-100	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	–	–	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.5	-1.9	-3.0	V
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =-10V, I _D =-15A	–	60	80	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =-4.5V, I _D =-10A	–	69	90	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1MHz	–	2478	–	pF
C _{oss}	Output Capacitance		–	88	–	pF
C _{rss}	Reverse Transfer Capacitance		–	62	–	pF
R _g	Gate Resistance	f=1MHz		16		Ω
Q _g	Total Gate Charge	V _{DS} =-50V I _D =-20A, V _{GS} =-10V	–	45	–	nC
Q _{gs}	Gate Source Charge		–	6	–	nC
Q _{gd}	Gate Drain Charge		–	13	–	nC
Switching Characteristics @ T _J = 25°C (unless otherwise stated)						
t _{d(on)}	Turn on Delay Time	V _{DD} =-50V, I _D =-1A, R _G =3.3Ω, V _{GS} =-10V	–	25	–	ns
t _r	Turn on Rise Time		–	13	–	ns
t _{d(off)}	Turn Off Delay Time		-	125	–	ns
t _f	Turn Off Fall Time		–	50	–	ns
Source Drain Diode Characteristics @ T _J = 25°C (unless otherwise stated)						
t _{rr}	Reverse Recovery Time	I _{SD} =-10A, V _{GS} =0V di/dt=100A/μs	–	35	–	nS
Q _{rr}	Reverse Recovery Charge		–	130	–	nC
V _{SD}	Forward on voltage③	I _{SD} =-10A, V _{GS} =0V	–	-0.84	-1.2	V

Notes: ① Pulse width limited by maximum allowable junction temperature

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.1mH, R_G = 16Ω, I_{AS} = -21A, V_{GS} = -10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

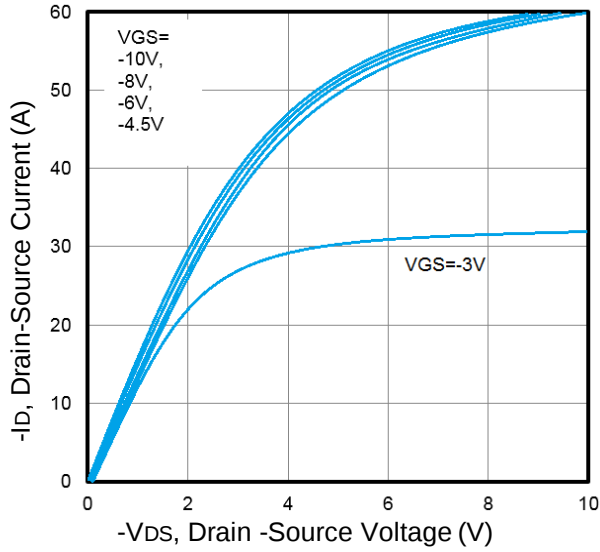


Fig1. Typical Output Characteristics

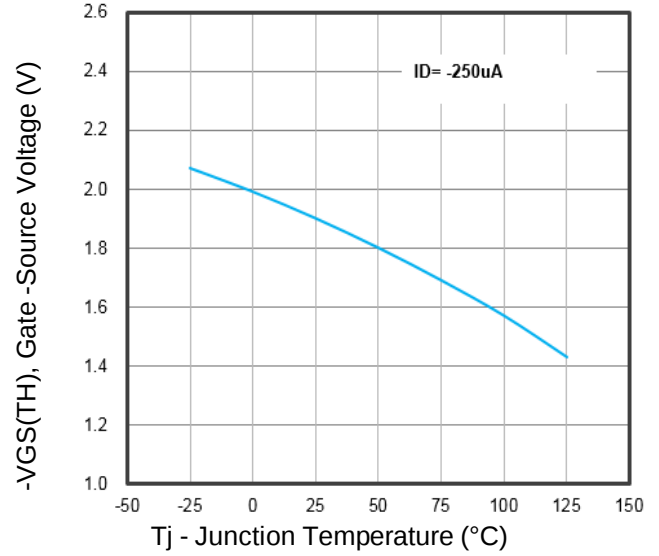


Fig2. -VGS(TH) Voltage Vs. Temperature

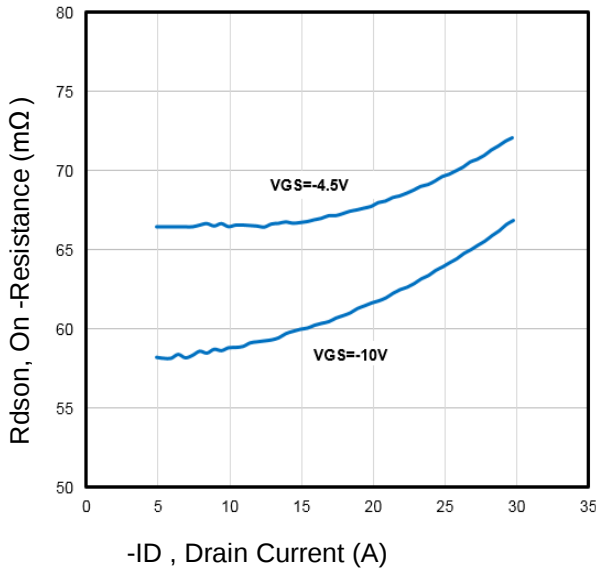


Fig3. On-Resistance vs. Drain Current and Gate Voltage

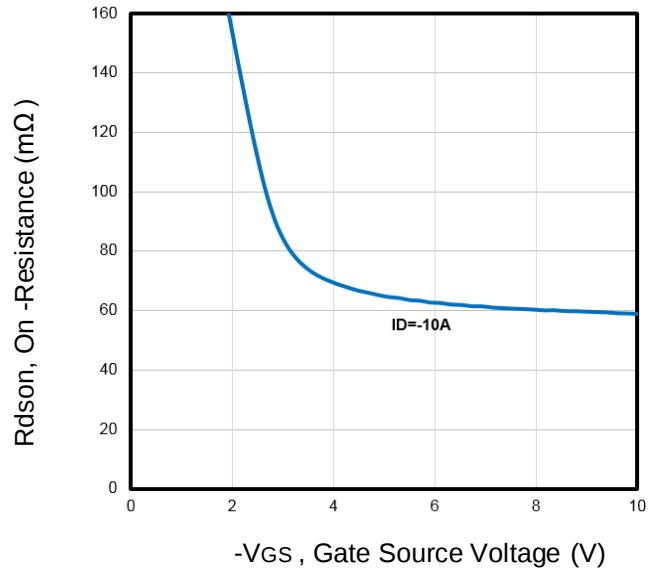


Fig4. On-Resistance vs. Gate Source Voltage

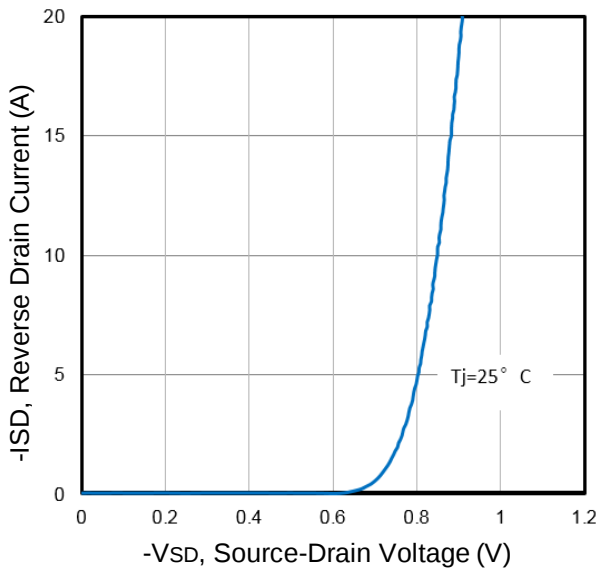


Fig5. Typical Source-Drain Diode Forward Voltage

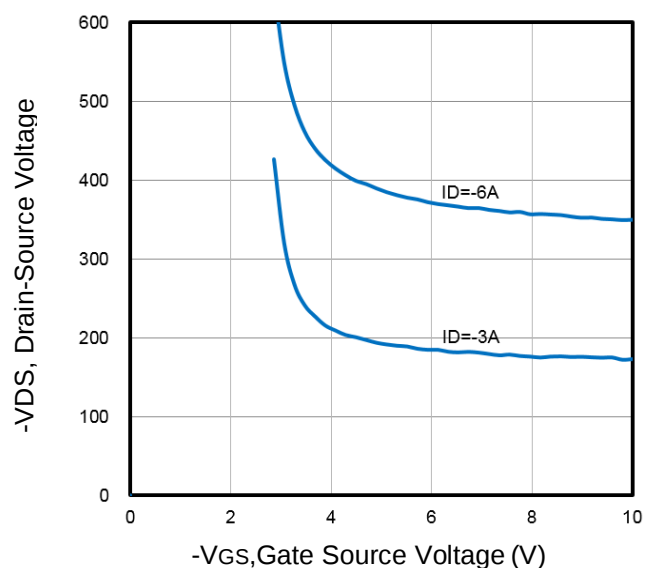


Fig6. Drain-Source Voltage vs Gate-Source Voltage

Typical Characteristics

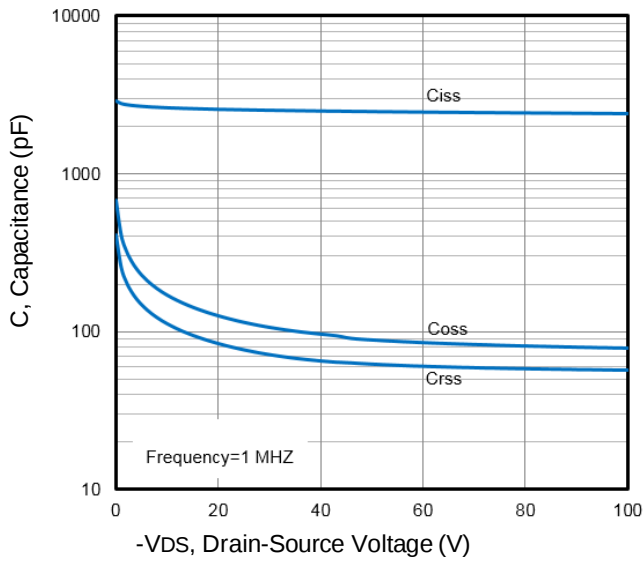


Fig7. Typical Capacitance Vs. Drain-Source Voltage

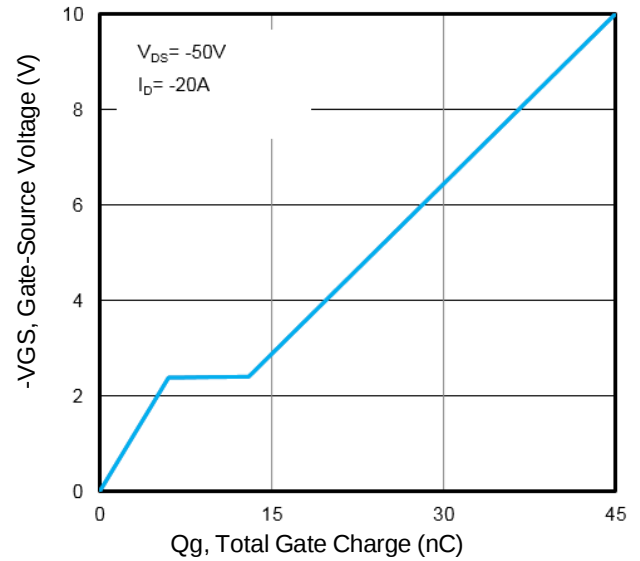


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

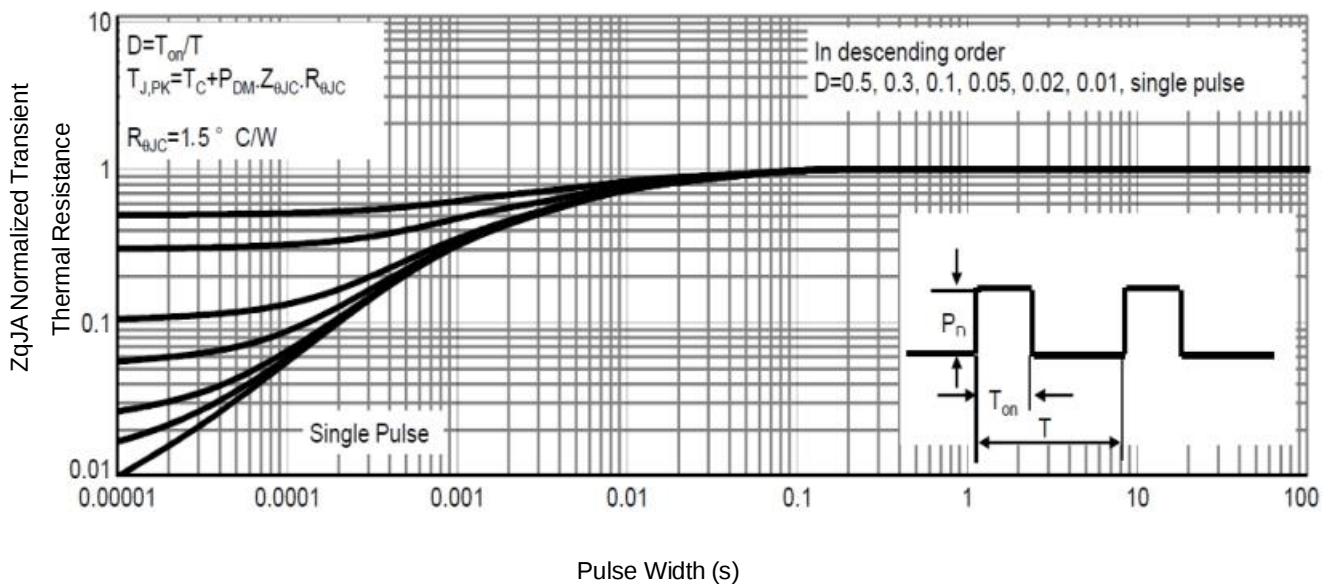


Fig9. Normalized Maximum Transient Thermal Impedance

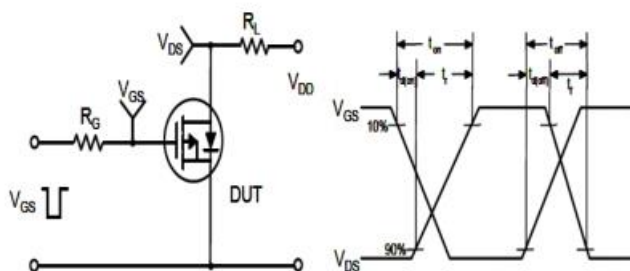


Fig10. Switching Time Test Circuit and waveforms

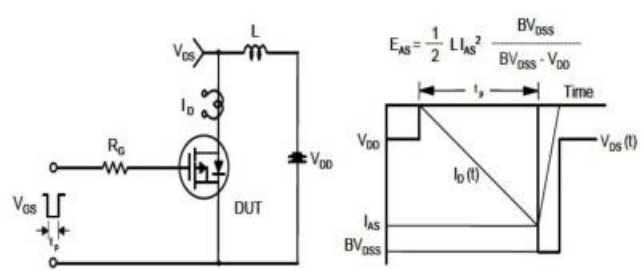
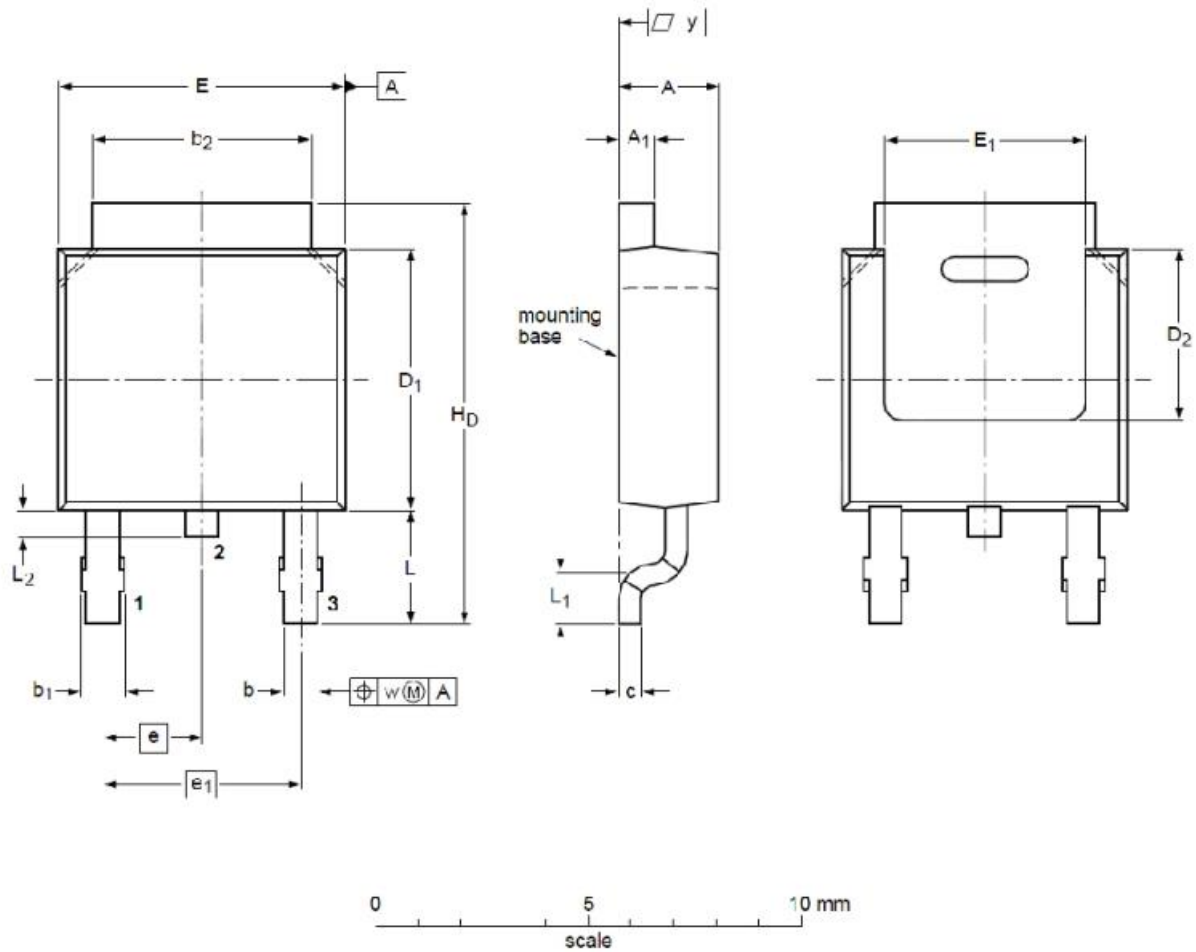


Fig11. Unclamped Inductive Test Circuit and waveforms

TO-252 Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.22	2.30	2.38	A ₁	0.4	0.53	0.65
b	0.68	0.78	0.89	b ₁	0.90	0.98	1.10
b ₂	5.20	5.33	5.55	c	0.45	0.5	0.55
D ₁	5.98	6.10	6.22	D ₂	--	4.00	--
E	6.47	6.60	6.73	E ₁	5.10	5.28	5.45
e	--	2.28	--	e ₁	--	4.57	--
H _D	9.60	10.08	10.40	L	2.75	2.95	3.05
L ₁	--	0.50	--	L ₂	0.50	--	1.10
w	--	0.20	--	y	0.20	--	--

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